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(54) OLED DISPLAY DEVICE WITH EMBEDDED CHIP DRIVING AND METHOD OF MANUFACTURING THE SAME

OLED-ANZEIGEVORRICHTUNG MIT EINGEBETTETER CHIP STEUERUNG UND VERFAHREN ZU DEREN HERSTELLUNG

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(73) Proprietors:
- **Global OLED Technology LLC**
  Herndon, VA 20171 (US)
- **Semprius Inc.**
  Research Triangle Park, NC 27709 (US)

(72) Inventors:
- **WINTERS, Dustin, Lee**
  Rochester, NY 14650 (US)
- **HAMER, John, William**
  Rochester, NY 14650 (US)
- **PARRETT, Gary**
  Rochester, NY 14650 (US)
- **BOWER, Christopher**
  Research Triangle Park, NC 27709 (US)
- **MENARD, Etienne**
  Research Triangle Park, NC 27709 (US)

(74) Representative: **Gunzelmann, Rainer**
Wuesthoff & Wuesthoff
Patentanwälte PartG mbB
Schweigerstraße 2
81541 München (DE)

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Description

FIELD OF THE INVENTION

[0001] The present invention relates to an electroluminescent display with semiconductor driving elements.

BACKGROUND OF THE INVENTION

[0002] In the simplest form, an organic electroluminescent (EL) device is comprised of an organic electroluminescent media disposed between first and second electrodes serving as an anode for hole injection and a cathode for electron injection. The organic electroluminescent media supports recombination of holes and electrons that yields emission of light. These devices are also commonly referred to as organic light-emitting diodes, or OLEDs. A basic organic EL element is described in U.S. Patent No. 4,356,429. In order to construct a pixelated OLED display device that is useful as a display such as, for example, a television, computer monitor, cell phone display, or digital camera display, individual organic EL elements can be arranged as pixels in a matrix pattern. These pixels can all be made to emit the same color, thereby producing a monochromatic display, or they can be made to produce multiple colors such as a three-pixel red, green, blue (RGB) display. OLED display devices have also been fabricated with active matrix (AM) driving circuitry in order to produce high performance displays. An example of such an AM OLED display device is disclosed in U.S. Patent No. 5,550,066. Active matrix circuitry is commonly achieved by forming thin film transistors (TFTs) over a substrate and the Organic electroluminescent media over the TFTs.

[0003] These TFTs are composed of a thin layer (usually 100 - 400 nm) of a semiconductor such as amorphous silicon or polysilicon. The properties of such thin film semiconductors are, however, often not sufficient for constructing a high quality OLED display. Amorphous silicon, for example, is unstable in that its threshold voltage (Vth) and carrier mobility shifts over extended periods of use. Polysilicon, often has a large degree of variability across the substrate in threshold voltage (Vth) and carrier mobility due to the crystallization process. Since OLED devices operate by current injection, variability in the TFTs can result in variability of the luminance of the OLED pixels and degrade the visual quality of the display. Novel compensation schemes, such as adding additional TFT circuitry in each pixel, have been proposed to compensate for TFT variability, however, such compensation adds complexity which can negatively impact yield, cost, or reduce the OLED emission area. Furthermore, as thin film transistor fabrication processes are applied to larger substrates such as used for large flat-panel television applications, the variability and process cost increase.

[0004] One approach to avoid these issues with thin film transistors is instead to fabricate conventional transistors in a semiconductor substrate and then transfer these transistors onto a display substrate. U.S. Patent Application Publication No. 2006/0055864 A1 by Matsumura et al. teaches a method for the assembly of a display using semiconductor integrated circuits (ICs) affixed within the display for controlling pixel elements where the embedded transistors in the ICs replace the normal functions performed by the TFTs of prior art displays. Matsumura teaches that the semiconductor substrate should be thinned, for example by polishing, to a thickness of between 20 micrometers to 100 micrometers. The substrate is then diced into smaller pieces containing the integrated circuits, hereafter referred to as 'chiplets'. Matsumura teaches a method cutting the semiconductor substrate, for example by etching, sandblasting, laser beam machining, or dicing. Matsumura also teaches a pick up method where the chiplets are selectively picked up using a vacuum chuck system with vacuum holes corresponding to a desired pitch. The chiplets are then transferred to a display substrate where they are nested in a thick thermoplastic resin.

[0005] The process taught by Matsumura, however, has several disadvantages. First, semiconductor substrates are typically 500 micrometers to 700 micrometers in thickness. Thinning the substrate in this fashion is difficult and at low thicknesses, the crystalline substrate is very fragile and easily broken. Therefore the chiplets are very thick, at least 20 micrometers according to Matsumura. It is desirable that the chiplets have a thickness of less than 20 micrometers, and preferably less than 10 micrometers. It is also desirable to include multiple metal wiring layers in the chiplet, thus the thickness of the semiconductor portion of the chiplet must be substantially thinner than the total thickness of the chiplet. The thick chiplets of Matsumura result in substantial topography across the substrate, which makes the subsequent deposition and patterning of metal layers over the chiplets difficult. For example, Matsumura describes concave deformations as one undesirable effect. Thinner chiplets would reduce these topography problems and facilitate formation of the subsequent layers above the chiplets.

[0006] Another disadvantage of the process taught by Matsumura is that the surface area of the chiplets must be large enough to be picked up by the vacuum hole fixture. As a result, the chiplets must have a length and a width that are larger than the minimum size of the vacuum hole. It is desirable that the surface area of the chiplet be small to enable high resolution displays and so that many chiplets can be produced on a single substrate thereby enabling a low unit production cost. It is also desirable that the shape of the chiplet be made to fit between pixels and not block light emission. Therefore, the chiplet should have a length or width that is narrow compared to the other dimension so that it can be placed in the spacing between the rows or the columns of pixels.

[0007] A process of transferring transistor circuits is taught in U.S. Patent No. 7,169,652 by Kimura. In this process, thin film transistors are formed and wired into circuits on a "transfer origin substrate" over a peeling

layer. The circuits are then flipped over and attached to a display substrate. The circuits are released from the transfer origin substrate by light irradiation of the peeling layer. This arrangement can be called a "pad-down" configuration. Because the process of Kimura requires the circuits to be flipped over in a pad-down configuration, electrical connections between the circuit and wiring lines formed on the display substrate are made by "local formation" of a conductive adhesive layer between the circuits and the substrate.

[0008] The process of Kimura has several disadvantages. First, it is difficult to achieve high quality semiconductors since thin film layers of semiconductor must be formed over a release layer. It is desirable to use high quality crystalline semiconductors, such as that of a crystalline silicon wafer to achieve the best transistor performance. Second, this approach requires the additional cost of forming in isolated beads of conductive adhesive. Third, it is difficult to achieve a high yield of good quality electrical connections by aligning to the small beads of conductive adhesive. It is therefore desirable to avoid the need for patterned conductive adhesive.

[0009] US 2006/0055864 A1 discloses a method for manufacturing an LCD display comprising the steps of: forming a pixel control device substrate and polishing it to the dimensions of 20 to 100 micrometers by polishing; attaching the pixel control device substrate onto the pick-up substrate; cutting the pixel control device substrate into a plurality of integrated circuits by cutting, etching, laser beam machining or sandblasting; picking up the integrated circuits through a vacuum chuck; transferring the integrated circuits into a display substrate and nesting them in a thick thermoplastic resin.

[0010] US 2007/0141809 A1 discloses a method for manufacturing a chip comprising: forming a semiconductor layer partially suspended above a semiconductor substrate and constrained thereto through temporary anchorages; dividing the layer into a plurality of portions laterally separated from one another; removing the anchorages.

[0011] US 2007/0257606 A1 discloses an OLED electroluminescent device comprising electrodes, an organic electroluminescent media, and a power transistor for controlling the organic electroluminescent media. A method for manufacturing such a device comprise the following steps: forming a first conductor layer and patterning it to form a plurality of power lines arranged in rows and columns; forming a second conductor layer and patterning it to form a plurality of power lines arranged in rows and columns; and electrically connecting the power bypass line to power lines.

SUMMARY OF THE INVENTION

[0012] It is an object of present invention to provide an improved method of producing an electroluminescent OLED display having chiplets driving elements where the chiplets are reduced in size and therefore cost. It is a further object of the present invention to reduce the thickness of the display having chiplets driving elements. It is a further object of this invention to provide ultra- thin chiplet driving elements which are interconnected to the OLED pixel elements using thin film metal deposition processes. This object is achieved by the method of claim 1. Advantageous embodiments of the invention are covered by the dependent claims.

BRIEF DESCRIPTION OF THE DRAWINGS

[0013]

FIG. 1 is a layout view of four pixels of an OLED display manufactured by a method according to the present invention;
FIG. 2A is a cross-sectional view along line X-X' of the device of Fig 1 in a pixel without a color filter;
FIG. 2B is a cross-sectional view along line U-U' of the device of Fig 1 in a pixel where a color filter is used;
FIG. 3A is a circuit schematic of the integrated circuit chiplet manufactured by a method according to the present invention;
FIG. 3B is a circuit schematic of an alternate embodiment of the integrated circuit chiplet manufactured by a method of the present invention;
FIG. 4 is a block diagram illustrating the process according to the present invention for forming a OLED display with chiplet driving circuitry;
FIG. 5 shows a layout view of a wafer containing chiplets prior to picking up the chiplets;
FIGS. 6A and 6B are cross sectional views along lines Y-Y' and Z-Z' of FIG. 5 respectively;
FIG. 7 is detailed cross-sectional view of a chiplet according to the present invention;
FIG. 8 is a plan view of the stamp used to pick up and transfer the chiplets;
FIG. 9 is a plan view of the chiplet stamp over the chiplets on the semiconductor substrate; and
FIG. 10 shows the Electro Static Damage prevention circuit diagram.

[0014] Since some device feature dimensions such as layer thicknesses are frequently in sub-micrometer ranges, the drawings are scaled for ease of visualization rather than dimensional accuracy.

DETAILED DESCRIPTION OF THE INVENTION

[0015] FIG. 1 shows a layout view of a group of four pixels (20a, 20b, 20c and 20d) elements of an OLED display device manufactured by a method according to the present invention. Each of the four pixels can be arranged to emit a different color, such as red, green, blue and white (RGBW). FIG. 1 represents a portion of a full display where the full display would be constructed of an array of such groups of pixels arranged in many rows

and columns. For example, a modem television would be constructed having 1920 rows and 1080 columns of such groups of pixels.

[0016] A chiplet 120 is arranged to control the electrical current to pixels 20a, 20b, 20c and 20d. A chiplet is a separately fabricated integrated circuit which is mounted and embedded into the display device. Much like a conventional microchip (or chip) a chiplet is fabricated from a substrate and contains integrated transistors as well as insulator layers and conductor layers which are deposited and then patterned using photolithographic methods in a semiconductor fabrication facility (or fab). These transistors in the chiplet are arranged in a transistor drive circuit, as will be describe in more detail below, to drive the electrical current to pixels of the display. A chiplet is smaller than a traditional microchip and unlike traditional microchips, electrical connections are not made to a chiplet by wire bonding or flip-chip bonding. Instead, after mounting each chiplet onto the display substrate, deposition and photolithographic patterning of conductive layers and insulator layers continues. Therefore, the connections can be made small, for example through using vias 2 to 15 micrometers is size. As the chiplet and connections to the chiplet are small enough to be placed within the area of one or more pixels which, depending on the display size and resolution, range from approximately 50 micrometers to 500 micrometers in size. Additional details about the chiplet and its fabrication and mounting processes will be described in below.

[0017] Each pixel is provided with a lower electrode, such as a lower electrode 161 a in pixel 20a. The emitting area of pixel 20a is defined by an opening 163a in an insulator formed over the lower electrode. The device includes multiple conductive elements formed in a first conductive layer which are arranged to facilitate providing electrical signals to the chiplet's transistor drive circuitry to enable the chiplet to control electrical current to the pixels. Chiplet 120 controls current to pixel 20a through a conductor 133a. For example, conductor 133a is connected to chiplet 120 through a via 143a and is also connected to lower electrode 161a through a via 153a. The device also includes a series of signal lines including, power lines, data lines, and select lines which are formed in the first conductive layer and transmit electrical signals from the edge of the display to the chiplets. Power lines are signal lines that provide a source of electrical current to operate the organic electroluminescent elements. Data lines are signal lines which transmit bright information to regulate the brightness of each pixel. Select lines are lines which selectively determine which rows of the display are to receive brightness information form the data lines. As such select lines and data lines are routed in an orthogonal manner.

[0018] Power is provided to the chiplet 120 by way of a power line 131. Two vias are provided for connection between the power line and the chiplet 120. A data line 135 is provided in the column direction for communicating a data signal containing brightness information to chiplet 120 for pixel 20a and pixel 20b. Similarly, a data line 136 is provided in the column direction for communicating a data signal containing brightness information to chiplet 120 for pixel 20b and pixel 20d. In an alternate embodiment, discussed in more detail below, the data lines 135 and 136 and the power line 131 can be connected to the chiplet 120 by only a single via for each line. A select line segment 137a is provided in the row direction for communicating a row select signal to chiplet 120 for pixel 20a and pixel 20b. The row select signal is used to indicate a particular row of pixels and is synchronized with the data signal for providing brightness information. Thus the row select signal and the data signals are provided in orthogonal directions. Chiplet 120 communicates the row select signal from select line segment 137a to a select line segment 137b by way of an internal pass-thru connection on the integrated circuit. Select line segment 137b then communicates the row select signal to subsequent chiplets arranged in the same row. Similarly a select line segment 138a is provided in the row direction for communicating a row select signal to chiplet 120 for pixel 20c and pixel 20d. Chiplet 120 communicates the row select signal from select line segment 138a to a select line segment 138b by way of another internal pass-thru connection on the integrated circuit. Select line segments 137a and 137b together serve to form a single select line, which is discontinuous. Connections between the select line segments is provided by the pass-thru connections in the chiplet. While only two segments are shown, the select line can contain a series of many such segments. Select line segments 138a and 138b similarly together serve to form a single discontinuous select line. In the preferred embodiment of the present invention, all of the select lines segments and data lines are formed from a single metal layer. Communication across the orthogonal array is then achieved by routing either the row select signal, the data signal, or both through the pass-thru connections on the chiplet.

[0019] FIG. 2A shows a cross sectional view of the OLED display device of FIG. 1 along line X-X', where pixel 20a is a white pixel, and thus needs no color filter. It can be seen that the device is constructed over a display substrate 100. Over display substrate 100, an adhesive layer 111 is provided. One preferred material for adhesive layer 111 is Benzocyclobutene (BCB), formed by spin coating to thickness of approximately 0.5 to 10 micrometers. Chiplet 120 is placed in the adhesive layer 111. The chiplet has a thickness (H), which is less than 20 micrometers and preferably less than 10 micrometers. Planarization layer 112 is provided to reduce the topography around chiplet 120 and facilitate continuous formation of a subsequent conductive layer. A planarization layer 112 is preferably formed at a thickness greater than the thickness (H) of the chiplet 120. A useful material for planarization layer 112 is Benzocyclobutene (BCB) formed by spin coating. It is particularly advantageous to use the same material for the adhesion layer 111 and the planarization layer 112 so as to reduce differences

in refractive index that can cause optical reflections at the interface of these two layers. Therefore by using the same material, the refractive index of the adhesion layer 111 and the planarization layer 112 layers are the same. Via 143a is opened in the planarization layer 112 and an optional insulator sub-layer 121 on chiplet 120 to provide access to a connection pad 353a. Formation of this via can be done using photolithography techniques and is facilitated if a photo-imagable BCB compound is used for planarization layer 112. Chiplet 120 is mounted over substrate 100 such that the connection pads, such as connection pad 353a, are facing upward. The arrangement can be called a "pad-up" configuration. In particular, the transistor circuitry in the chiplet (not shown) is disposed between the connection pads and the substrate 100. This arrangement is advantageous in that it provides convenient access to the connection pads for subsequent wiring layers.

[0020] Over planarization layer 112, a conductor layer (or wiring layer) is formed. This conductor layer is then patterned using conventional photolithography techniques into the select lines, data lines, and power lines, as well as the connectors between the chiplets and the anodes, such as conductor 133a. Electrical connection between the conductor layer and the chiplet 120 can then be readily made through vias, such as via 143a. This enables high quality, reliable electrical connectivity. Since the current to the pixels is provided by the wiring layer, it is preferred that this layer be constructed to have low resistance. In this regard, preferred materials for this layer include aluminum or aluminum alloys formed to a thickness of approximately 200 to 500 nm. Over this wiring layer, an insulator layer 113 is formed. Vias, such as via 153a, provide for connection to the wiring layer from above. Lower electrode 161 a is provided over insulator layer 113. In this bottom emitter configuration, lower electrode 161 a is made to be at least partially transparent. Useful materials include transparent conductive oxides such as Indium Tin Oxide (ITO) or Aluminum doped Zinc Oxide (AZO) or the like. Thin metals such as less than 25 nm of aluminum, silver, or the like can also be used. Over the edges of lower electrode 161 a, an insulator layer 114 is formed. This insulator layer 114 can be constructed, for example, of a photo-patterned polymer and serves to prevent high electric fields at the edges of the lower electrode 161 a. Similar insulator layers for this purpose are described in U.S. Patent No. 6,246,179. Opening 163a is provided in the insulator layer to provide for contact to the lower electrode 161 a.

[0021] Above lower electrode 161 a, an organic electroluminescent medium 165 is formed. There are many different organic electroluminescent media configurations known in the art that can be successfully applied to the present invention by one skilled in the art. Although the organic electroluminescent medium 165 is shown as a single layer, it preferably includes a plurality of sublayers such as a hole transporting sub-layer and an electron transporting sub-layer. Organic electroluminescent medium 165 can include additional sub-layers such as hole injecting sub-layers, electron injecting sub-layers, or specialized light emitting sub-layers. For the organic electroluminescent media 165, a common broadband (or white) light source which emits light at all the various wavelengths used by all the differently colored pixels is preferably used to avoid the need for patterning the organic electroluminescent media between light producing units. Colored pixels are achieved by aligning color filter elements with light producing elements. Some examples of organic EL media layers that emit broadband or white light are described, for example, in U.S. Patent No. 6,696,177. However, the present invention can also be made to work where each pixel has one or more of the organic electroluminescent media sub-layers separately patterned for each pixel. The organic EL media is constructed of several sublayers such as; a hole injecting sublayer, a hole transporting sublayer that is disposed over the hole injecting sublayer, a light-emitting sublayer disposed over the hole transporting sublayer, and an electron transporting sublayer disposed over the light-emitting sublayer. Alternate constructions of the organic electroluminescent media 165 having fewer or more sublayers can also be used to successfully practice the present invention.

[0022] Over organic electroluminescent medium 165, an upper electrode 169 is formed. Although shown as a single layer, upper electrode 169 can also include a plurality of sub-layers. Several upper electrode configurations are known in the art and can be applied to the present invention by one skilled in the art. One configuration for upper electrode 169 includes a sub-layer of Li or LiF approximately 0.5 nm thick in contact with the organic electroluminescent medium 165 for facilitating electron injection followed by a sub-layer of Al approximately 100 to 400 nm thick. Other features such as a moisture barrier encapsulation (not shown) or desiccant (not shown) commonly used in the art of fabricating OLED devices can also be included. Current flow between the lower electrode 161 a and the upper electrode 169 through the organic electroluminescent medium 165 results in light emission 50.

[0023] FIG. 2B shows a cross sectional view of the OLED display device of FIG. 1 along line U-U', where pixel 20b has a colored filter. A color filter 190a is placed under the light emitting area, and can be deposited before the adhesive layer 111 as shown. In an alternative embodiment the color filters can be placed on top of the adhesive. For an RGBW type display, the white pixels are can be constructed without color filters. Color filters can be formed by methods such as spin coating and are approximately 1 to 3 micrometers in thickness. It is preferred that the color filter be placed under the planarization layer 112 so that the planarization layer serves to planarize both the color filters and the chiplet 120. It is preferred that the color filters are formed prior to mounting the chiplets. Since the chiplets are relatively thick, their presence can impair proper spin coating of the color fil-

ters, so that device performance and yield are enhance by stamping the chiplets after forming the color filters. Furthermore, the color filters process can be inspected and defective devices discarded prior to placing the chiplets so as to reduce the chance of wasting chiplets, thereby reducing overall production cost.

[0024] FIG. 3A illustrates a schematic drawing of an integrated circuit 300 provided on each chiplet according to a method of the present invention. Integrated circuit 300 is arranged to drive four independent OLED pixel elements. Integrated circuit 300 includes four select transistors (320a, 320b, 320c and 320d), four storage capacitors (330a, 330b, 330c and 330d) and four drive transistors (340a, 340b, 340c and 340d). Other circuits with more or less components can also be employed to successfully practice the present invention. These components are connected to several connection pads arranged in two rows including connection pads 351a, 351b, 353a, 353b, 354a, 355a and 356a arranged in a first row and connection pads 352a, 352b, 353c, 353d, 354b, 355b and 356b arranged in a second row. Connections pads 353a, 353b, 353c and 353d are provided for connection to the lower electrode (anode) of the organic light emitting diode element of each pixel. These connection pads are electrically connected to drive transistors 340a, 340b, 340c and 340d respectively. Connection pads 356a and 356b are arranged for connection to an external power supply line, are electrically connected by pass-thru connection 316 and are electrically connected to all of the drive transistors 340a, 340b, 340c and 340d. Connection pads 351a and 351b are arranged for connection to a first external select line, are electrically connected by a pass-thru connection 311 a and are electrically connected to the gates of select transistors 320a and 320b. Connection pads 352a and 352b are arranged for connection to a second external select line, are electrically connected by pass-thru connection 311b and are electrically connected to the gates of to select transistors 320c and 320d. Connection pads 354a and 354b are arranged for connection to a first external data line, are electrically connected by a pass-thru connection 314a and are electrically connected to select transistors 320a and 320c. Connection pads 355a and 355b are arranged for connection to a first external data line, are electrically connected a by pass-thru connection 314b and are electrically connected to select transistors 320b and 320d.

[0025] In order for the external select lines to address the rows of pixels of the display and the external data lines to address the columns of the display these lines must be arranged in an orthogonal pattern. It is desirable that these external lines be formed from a single metal layer to avoid additional manufacturing steps. This is achieved by routing either the data signal or the select signal through the pass-thru connections on the chiplet. In the case shown, the select signals, the data signals, and the power signal are all provided with pass-thru connections. The external select lines are discontinuous and require the pass-thru connections to complete the connection. The external data lines and power lines however are continuous. In this case, providing two connection pads with a pass-thru connection for each of the two data signals and power signals has an advantage of redundancy. That is, if one of the connections between the connection pad and the external data lines or the external power lines is not fully formed or is otherwise incomplete, the device will continue to function.

[0026] In alternate embodiments of the present invention, pass-thru connections can be provided for only the select signal and not the data signal or vice versus. The pass-thru connection for the power signal can also be optionally eliminated. In addition to removing the pass-thru connections, one of the two connection pads associated with each of the removed pass-thru connections can also be removed. One such alternate embodiment is shown in FIG. 3B. This alternate embodiment has an advantage that surface area of the chiplet needed for circuitry and connection pads is reduced. However, this alternate embodiment losses the advantage of redundant connections for the data signal and power signal.

[0027] FIG. 1 to FIG. 3B show the preferred embodiment where the chiplet drives four pixels where the four pixels includef pixels that emit red, green, blue, and white light.

[0028] FIG. 4 is a block diagram describing the process according to the present invention for making an OLED display. The process 500 begins with step 510 by forming integrated circuits. These integrated circuits are arranged in a configuration to drive one or more pixels of the OLED display. The integrated circuit is formed from a silicon-on-insulator type (SOI) substrate using conventional, known integrated circuit fabrication techniques. Preferred SOI substrates include a crystalline silicon layer formed over an insulator layer, such as silicon dioxide, which is in turn formed over a bulk crystalline silicon wafer. The silicon dioxide layer is commonly referred to as the "buried oxide" or "BOx". There are a variety of methods known in the art for producing SOI wafers. Some of these methods including bonding a first silicon wafer with a silicon dioxide layer to a second silicon wafer followed by cleaving or thinning the second silicon wafer such that a thin film of crystalline silicon remains over the silicon dioxide layer. Such SOI wafers are commercially available from a variety of suppliers. Also, integrated circuits formed on SOI substrates useful for practicing the present invention can also be purchased from a variety of commercial suppliers, known as foundries. For purposes of this invention, this substrate used for forming the integrated circuit for the chiplets is hereafter referred to as the "integrated circuit substrate".

[0029] In step 520, a release etch is formed to partially separate the chiplets from the integrated circuit substrate. This step is further illustrated in the layout view of the chiplet partially attached to the integrated circuit substrate shown in FIG. 5 and cross sectional views of FIG. 6A and FIG. 6B. FIG. 6A is a cross sectional view from FIG. 5 along line Y-Y' and FIG. 6b is a cross sectional

view from FIG. 5 along line Z-Z'. Chiplet 120 is formed from an integrated circuit substrate which is of the silicon on insulator type. The silicon on insulator substrate consists of a semiconductor layer 605, preferable less than 10 micrometers in thickness and more preferably between 0.05 and 5 micrometers in thickness, separated from an integrated circuit substrate bulk 601 by a buried oxide with a thickness of between 0.1 to 3.0 micrometers. In the area of the chiplet, the semiconductor layer contains the semiconductor portions, including doped regions and wells, used in forming the source and drain regions of the transistors. Over the semiconductor layer, circuitry layers 670 are formed which contain chiplet-conductor sub-layers, such as a chiplet-conductor sub-layer for forming gate electrodes and one or more chiplet-conductor sub-layers serving to form electrical connections between the transistors. Circuitry layers 670 include the connection pads, such as connection pads 353b, 353d, 354a and 354b formed in one of chiplet-conductor sub-layer.

[0030] The circuitry layers 670 and semiconductor layer 605 are further illustrated in the cross-sectional view of the chiplet 120 shown in FIG. 7. The circuitry layers 670 also include several insulator sub-layers such as a gate insulator sub-insulator 124 and interlayer insulator sub-layers 123, 122, and 121. These insulator sub-layers can be constructed of materials such as silicon dioxide or other known insulator materials. The chiplet also includes a plurality of chiplet-conductor layers. The first chiplet-conductor layer is arranged to form gate electrodes, such as a gate electrode 127. Doped regions in semiconductor layer 605, such as a doped region 606d, form sources and drains of transistors corresponding to the gate electrodes. A second chiplet conductor layer is provided for forming connections between transistors, such as the pass-thru connection 314a. The connection pads, such as connection pads 351a and 352a, are preferably formed in a third chiplet-conductor layer. This preferred configuration permits efficient layout of the wiring in the second chiplet-conductor layer while permitting dense packing of connection pads in the third chiplet-conductor layer. However, in alternate embodiments fewer or more chiplet-conductor layers can be employed. The thickness of the circuitry layers 670 depends on the number of chiplet-conductor sub-layers and is preferably between 1 micrometer and 15 micrometers. The total thickness of the chiplet (H) is then combination of the thickness of the semiconductor layer 605 and the circuitry layers 670 and is less than 20 micrometers.

[0031] Turning back to FIG. 6A and 6B, trenches, such as a trench 640, are formed around each chiplet, such as chiplet 120. These trenches are etched through the semiconductor layer 605, exposing the buried oxide layer. Anchor areas, such as anchor area 620, are provided between chiplets. The chiplets are attached to the anchor areas by small microbridges, such as microbridge 610 as described in U.S. Patent Application Serial No. 11/421,654. Prior to forming the trenches, a protection layer (not shown) of a material such as a photoresist or silicon nitride layer is formed over the integrated circuitry as described in U.S. Patent Application Publication No. 2008/0108171. A release etch is then performed using an etchant such as hydrofluoric acid (HF) to remove the portion of the buried oxide layer disposed under the chiplet and microbridges, leaving a buried oxide portion 630 under the anchors. The protection layer can then removed, exposing the chiplet connection pads. Chiplet 120 has a width (W) and length (L). The anchor area 620 has a width (l) which is preferably greater than W to permit the buried oxide to be complete removed from under the chiplet while not completely etching the buried oxide under the anchor leaving buried oxide portion 630.

[0032] Turning back to FIG. 4, adhesion layer 111 is applied to the display substrate 100 in step 530. The adhesive can be BCB or other common photoresist materials as described above.

[0033] The chiplets are picked up in step 540 with a stamp as described in U.S. Patent Application Serial No. 11/145,574. The stamp is preferably constructed of a conformable material such as poly(dimethyl siloxane) (PDMS) that has its undersurface formed into posts. An example stamp 800 is shown in FIG. 8. Stamp 800 contains a variety of raised posts, such as post 810. The spacing of the posts is predetermined to be a geometric multiple (integer or integer ratio) of the spacing of the chiplets on the integrated circuit substrate as well as the pixels spacing on the display substrate. For example, the alignment of the stamp to the chiplets to the integrated circuit substrate is shown in FIG. 9 where the posts correspond to every second chiplet (such as chiplet 120) in the x direction and every fourth chiplet in the y direction. The posts on the stamp pad can pick up a portion of the chiplets in one stamping operation. Multiple stamping operations can then be used to populate the entire display with chiplets. This has the advantage that due to the area of high utilization efficiency of the integrated circuit substrate area, the integrated circuit substrate area can be much smaller than the area of the display. In the pickup operation, the stamp is aligned so the posts 810 are located over the chiplets 120. The chiplets are then quickly detached from the silicon on insulator substrate. As described in U.S. Patent Application Serial No. 11/423,192, kinetic control of the adhesion forces between the stamp and the chiplets enable the controlled fracture of the supporting microbridges 610. The van de Waal's force between the stamp and the chiplet causes the chiplets to remain in contact with the stamp after the microbridges are broken. This method of picking up the chiplets enables the chiplets to be very small in area. For example, a chiplet with length or width dimensions of 50 micrometers or less can be ready picked up using this method. Such dimensions are difficult to achieve using a vacuum suction apparatus as the vacuum suction opening must be smaller than the chiplet dimension. This technique also permits large arrays of such chiplets to be simultaneously transferred while maintaining good dimensional

spacing and alignment between the chiplets.

[0034] In step 550, the stamp with the chiplets is aligned to the target location on the display substrate 100 and lowered so the chiplets 120 are in contact with the adhesion layer 111. The bond with the adhesive is stronger than the van de Waal's force so the chiplets remain on the display substrate. The stamp is then withdrawn, leaving the chiplets adhered to the display substrate. The adhesive can then be cured. Optionally, the adhesive can also be removed in areas not under the chiplet. At this stage the chiplets are effectively mounted to the display substrate.

[0035] In step 560, the planarization layer 112 is applied to the substrate, covering the chiplets. The BCB layer is preferably greater in thickness than the chiplets, which is beneficial in reducing overall topography (variations in surface height) on the display substrate. The planarization layer is patterned to open the vias, such as via 143a over the chiplet as described above. In the preferred embodiment, the planarizing material is itself a photo resist material, such as photoimagable BCB, that can be used also as a mask to permit etching of the insulating sub-layer 121 on the chiplet 120 in order to expose the metal connection pads, such as connection pad 353a in the chiplet. At this stage, the chiplet is effectively embedded in the display device.

[0036] In step 570, a conductor layer is deposited over top of the planarization layer, and then the metal layer is patterned to form wires. Standard photolithography methods and etching can be used to pattern the wires. Alternatively the metal layer can be deposited in a pattern-wise fashion using methods such as ink-jet deposition of silver nano-particles.

[0037] In the case of a bottom emission OLED display, a transparent lower electrode 161 a is required. One approach to form such a patterned electrode is to deposit another insulator layer 113 of photoresist and to open vias exposing for connection to the underlying metal layer, e.g. 153a. The transparent lower electrode 161 a is then deposited, for example by sputtering, using a common transparent conductive oxide such as ITO or IZO. This is patterned using standard etching methods. Alternative transparent electrode materials exist including conductive polymeric materials such as PDOT/PSS copolymers. In the alternative embodiment of a top-emission display, the patterned conductor layer could be used to form the reflective lower electrodes, eliminating the need for a separate conductor layer and inter-layer insulator layer 113.

[0038] The emission areas of each pixel are defined by opening 163 a in insulator layer 114 that can be formed of a photoimagable material.

[0039] In step 580, the electroluminescent media 165 layers of materials is formed. In the preferred embodiment these are small molecule materials and a typical stack contains layers for hole injection, hole transport, recombination and light emission, electron transport and electron injection. Multiple stack can also be used with connecting layers. A preferred method of forming the organic electroluminescent media layers is by evaporation from a crucible or linear evaporation source. Alternatively these materials can be polymeric and deposited by methods known in the art such a spin coating or inkjet coating.

[0040] In step 590, the upper electrode 169 is formed. In the preferred embodiment this electrode is not patterned in the pixel area but is continuous and electrically common across all the pixels. The upper electrode can be deposited by evaporation or sputtering. For a bottom emitting configuration, preferred materials include aluminum, a stack of aluminum over lithium or lithium fluoride, or magnesium silver alloys. In an alternate top emitting embodiment, the upper electrode can be made to be transparent using materials such as transparent conductive oxides like ITO or thin metals such as less than 25 nm of aluminum or silver. The circuit in the chiplet serves to regulate the current flowing vertically through the OLED stack between lower electrode 161 a and upper electrode 169, producing the light emission 50 at desired intensities.

[0041] FIG. 5 shows a plan view of the chiplets 120 on the mother wafer prior to pickup in step 540. After etching to release the chiplets in step 520, the chiplets remain attached by microbridges 610. The rows of chiplets are separated by the anchor area 620 that remain attached to the substrate below the etched layer. A cross section of the chiplet through Y-Y' in FIG. 5 is shown in FIG. 6A and a cross section through Z-Z' is shown in FIG. 6B. The buried oxide portion 630 is completely removed from under the chiplet 120 but partially remains under the anchor area. The microbridges 620 mechanically support the chiplet after the etching is complete.

[0042] As previously described and further illustrated in FIG. 5, each chiplet has connection pads arranged in two rows including connection pads 351a, 351b, 353a, 353b, 354a, 355a and 356a arranged in a first row and connection pads 352a, 352b, 353c, 353d, 354b, 355b and 356b arranged in a second row. The rows are arranged parallel to the length (L) direction. It is desirable that the width (W) be made small in order to facilitate the release etch. Therefore it is preferable that the chiplet be constructed with either one or two rows of vias. The transistor and wiring circuitry within the chiplet can be fabricated using currently available semiconductor patterning technology. For example, semiconductor fabrication facilities can process feature sizes of 0.5 micrometers, 0.35 micrometers, 0.1 micrometers, 0.09 micrometers, 0.065 micrometers, or smaller. The size of the pads, however, is determined by the alignment and feature sizes of the metallization layers formed on the display substrate and is relatively large. For example, line, space, and via sizes of 5 micrometers with alignment accuracies of +/- 5 micrometers would be compatible with chiplet connection pads that were 15 micrometers on a side (S) and spaced at 20 micrometers in pitch (P). Therefore, in the present embodiment of the invention, the overall size of the chiplet is dominated by the size and arrangement of the con-

nection pads. It is desirable that the size of the chiplet be made small so that many chiplets can be made simultaneously on the same integrated circuit substrate.

[0043] The connections to the chiplets made on the display substrate are shown in FIG. 1. It is desirable that the surface area of the display substrate covered by the chiplet and the wiring be made small so that the surface area available for emission of the pixels is large. In order to facilitate the connections to the chiplet while keeping the surface area of the wiring small, the arrangement of the connection pads on the chiplets is specifically selected. For example, the connection pads associated with the select line segments (137a, 137b, 138a, 138b) are arranged at the ends (first and last) of each row of connections pads. This avoids the need to bend the select line segments which can then be made small.

[0044] The data lines 135 and 136 are routed in a direction perpendicular to that of the select lines segments. In a preferred arrangement shown in FIG. 1, the data lines pass over the chiplet 120 in a continuous fashion. As such, it is desirable that the chiplet 120 be arranged so that is shorter width (W) dimension be aligned parallel to direction of the data lines. The longer length (L) direction is therefore preferably aligned parallel to the select lines. The power line 131 is also preferably routed in a continuous fashion in a direction perpendicular to that of the select lines segments and parallel to the shorter width (W) dimension of the chiplet 120. These layout arrangements result in a large portion of the area of the chiplet under the signal lines being that of the connection pads and reduces wasted non-connection pad areas covered by the signal lines so that the chiplet can be made small and the surface area of the display substrate covered by the chiplets can also be made small. It is also preferably the power line be arranged so as to be centered over the chiplet as shown to simplify wiring to the pixels on each side of the power line.

[0045] A pixel drive circuit of an alternate embodiment useful for protecting against electrostatic damage is shown in FIG. 10. Multiple pixel drive circuits can be included on the chiplet to drive multiple pixels. The pixel drive circuit consists of a drive transistor 340a, a select transistor 320a, a storage capacitor 330a and a diode 321 for electrostatic discharge (ESD) protection. In the configuration shown all the transistors are p-mos and only a single power connection pad 356a is needed. If CMOS transistors were used then another power connection would be required which would add additional wiring in the panel. The power connection pad 356a is connected to the doped well regions of the semiconductor bulk corresponding to transistors 320a and 330a and also to the semiconductor bulk of the chiplet through connections 322. The ESD diode 321 is connected to connection pad 351a and power connection pad 356a. It provides protection for the gate of select transistor 320a from voltage transients in manufacturing of the chiplet, during printing of the chiplet, during manufacturing of the display and during operation.

PARTS LIST

[0046]

20a	white pixel
20b	pixel with color filter
20c	pixel
20d	pixel
50	light emission
100	display substrate
111	adhesion layer
112	planarization layer
113	insulator layer
114	insulator layer
120	chiplet
121	insulator sub-layer
122	insulator sub-layer
123	insulator sub-layer
124	insulator sub-layer
127	gate electrode
131	power line
133a	conductor
135	data line
136	data line
137a	select line segment
137b	select line segment
138a	select line segment
138b	select line segment
143a	via
153a	connection pad
161a	lower electrode
163a	opening
165	organic electroluminescent medium
169	upper electrode
190a	color filter
300	integrated circuit
311a	pass-thru connection
311b	pass-thru connection
314a	pass-thru connection
314b	pass-thru connection
316	pass-thru connection
320a	select transistor
320b	select transistor
320c	select transistor
320d	select transistor
321	ESD protection diode
322	connection to well and chiplet substrate
330a	storage capacitor
330b	storage capacitor
330c	storage capacitor
330d	storage capacitor
340a	drive transistor
340b	drive transistor
340c	drive transistor
340d	drive transistor
351a	connection pad
351b	connection pad
352a	connection pad

352b	connection pad
353a	connection pad
353b	connection pad
353c	connection pad
353d	connection pad
354a	connection pad
354b	connection pad
355a	connection pad
355b	connection pad
356a	connection pad
356b	connection pad
500	process
510	step
520	step
530	step
540	step
550	step
560	step
570	step
580	step
590	step
601	integrated circuit substrate bulk
605	semiconductor layer
606d	doped region
610	microbridge
620	anchor area
630	buried oxide portion
640	trench
670	circuitry layers
800	stamp
810	posts

Claims

1. A method for manufacturing an OLED display having a plurality of current driven pixels (20a, 20b, 20c, 20d) arranged in rows and columns disposed over a display substrate (100), such that when current is provided to a pixel it produces light, the OLED display comprising:

(a) each pixel having first and second electrodes (161a, 169) and a current responsive electroluminescent media (165) disposed between the first and second electrodes;
(b) at least one chiplet (120, 300) having a thickness less than 20 micrometers; including transistor drive circuitry (340a, 340b, 340c, 340d) configured for controlling the operation of exactly four pixels, the chiplet being mounted on the display substrate (100) and having connection pads (353a, 353b, 353c, 353d); wherein the chiplet (120) has a width (W) and a length (L) that is greater than the width (W), and the connection pads of the chiplet (120) are arranged in a first and second row along the direction of the length (L);
(c) a planarization layer (112) disposed over at least a portion of the chiplet;
(d) a first conductive layer (133a) disposed over the planarization layer and connected to at least one of the connection pads of the chiplet; and
(e) means for providing electrical signals through the first conductive layer and at least one of the connection pads of the chiplet so that the transistor drive circuitry of the chiplet controls current to the four pixels;
(f) a power line (131) arranged parallel to the width (W) of the chiplet; the method comprising the following steps:

- using a silicon-on-insulator SOI technique, forming the chiplets (120) as integrated circuits from an integrated circuit substrate (601);
- performing undercut release etch to partially separate the chiplets from the integrated circuit substrate;
- providing the display substrate (100) with an adhesion layer (111);
- picking up the chiplets with a stamp (800);
- stamping the chiplets into the adhesion layer;

and, for each chiplet:

- forming the planarization layer (112);
- patterning the planarization layer (112) to open first vias (143a);
- forming the first conductive layer (133a) in the first vias (143a);
- forming the first electrode (161a) and connecting the first electrode (161a) to the first conductive layer (133a) though second vias (153a);
- forming the current responsive electroluminescent media (165); and
- forming the second electrode (169).

2. The method of claim 1, wherein the first electrode is formed in a second conductive layer that is different than the first conductive layer.

3. The method of claim 2 further including an insulator layer disposed between at least a portion of the first electrode and the first conductive layer.

4. The method of claim 2, wherein the first electrode is connected to the chiplet by the first conductive layer.

5. The method of claim 1, wherein the first electrode is formed in the first conductive layer.

6. The method of claim 1, wherein the OLED display further includes one or more data signal lines (135,

136), and one or more select lines (137a, 137b) and wherein said power line, said one or more data signal lines and said one or more select lines are formed in the first conductive layer and connected to corresponding connection pads on the chiplet.

7. The method of claim 6, wherein the chiplet further comprises an electrical pass-thru connection and wherein either the select line or data signal line is discontinuous and connected to the electrical pass-thru connection in the chiplet.

8. The method of claim 1, wherein the OLED display further includes a signal line which is discontinuous and connected to the first and last connection pads in each row of connection pads of the chiplet

9. The method of claim 1, wherein the four pixels controlled by the chiplet each have different colors.

10. The method of claim 1, wherein the transistor drive circuitry of each chiplet includes a first driving transistor having a first channel ratio for controlling a first pixel and a second driving transistor having a second channel ratio for controlling a second pixel where the first pixel has a different color than the second pixel and the first channel ratio is different than the second channel ratio.

11. The method of claim 1, wherein the power line (131) is disposed over the center of the chiplet (120).

Patentansprüche

1. Verfahren zum Herstellen eines OLED-Displays, das eine Mehrzahl von durch Strom angetriebene Pixel (20a, 20b, 20c, 20c) umfasst, die in Reihen und Spalten angeordnet sind, welche über einem Displaysubstrat (100) angeordnet sind, so dass, wenn einem Pixel Strom zugeführt wird, es Licht produziert, wobei das OLED-Display umfasst:

(a) jeden Pixel, der erste und zweite Elektroden (161a, 169) und ein auf Strom reagierendes elektrolumineszentes Medium (165), das zwischen den ersten und zweiten Elektroden angeordnet ist, aufweist;
(b) mindestens ein Chiplet (120, 300), das eine Dicke von weniger als 20 Mikrometer hat und einen Transistorantriebsschaltkreis (340a, 340b, 340c, 340d) umfasst, der dazu eingerichtet ist, den Betrieb von exakt vier Pixeln zu steuern, wobei das Chiplet an dem Displaysubstrat (100) angebracht ist und Verbindungsplättchen (353a, 353b, 353c, 353d) aufweist, wobei das Chiplet (120) eine Breite (W) und eine Länge (L) hat, die größer ist als die Breite (W), und die Verbindungsplättchen des Chiplets (120) in einer ersten und einer zweiten Reihe entlang der Richtung der Länge (L) angeordnet sind;
(c) eine Planarisierungsschicht (112), die über zumindest einem Abschnitt des Chiplets angeordnet ist;
(d) eine erste leitfähige Schicht (133a), die über der Planarisierungsschicht angeordnet und mit mindestens einem der Verbindungsplättchen des Chiplets verbunden ist; und
(e) ein Mittel zum Bereitstellen elektrischer Signale durch die erste leitfähige Schicht und mindestens eines der Verbindungsplättchen des Chiplets, so dass der Transistorantriebsschaltkreis des Chiplets Strom zu den vier Pixeln steuert;
(f) eine Stromleitung (131) die parallel zu der Breite (W) des Chiplets angeordnet ist;

wobei das Verfahren die folgenden Schritte umfasst:

- Verwenden einer Silizium-auf-Isolator-SOI-Technik, Ausbilden der Chiplets (120) als integrierte Schaltungen aus einem integrierten Schaltungssubstrat (601);
- Durchführen einer Hinterschnittlöseätzung zum partiellen Trennen der Chiplets von dem integrierten Schaltungssubstrat;
- Versehen des Displaysubstrats (100) mit einer Klebeschicht (111);
- Aufnehmen der Chiplets mit einem Stempel (800);
- Stempeln der Chiplets in die Klebeschicht;

und, für jedes Chiplet:

- Ausbilden der Planarisierungsschicht (112);
- Mustern der Planarisierungsschicht (112) zum Öffnen erster Durchgangsleitungen (143a);
- Ausbilden der ersten leitfähigen Schicht (133a) in den ersten Durchgangsleitungen (143a);
- Ausbilden der ersten Elektrode (161a) und Verbinden der ersten Elektrode (161a) mit der ersten leitfähigen Schicht (133a) durch zweite Durchgangsleitungen (153a);
- Ausbilden des auf Strom reagierenden elektrolumineszenten Mediums (165); und
- Ausbilden der zweiten Elektrode (109 60).

2. Verfahren gemäß Anspruch 1, bei dem die erste Elektrode in einer zweiten leitfähigen Schicht ausgebildet ist, die verschieden von der ersten leitfähigen Schicht ist.

3. Verfahren gemäß Anspruch 2, das ferner eine Isolatorschicht umfasst, die zwischen zumindest einem Abschnitt der ersten Elektrode und der ersten leitfähigen Schicht angeordnet ist.

4. Verfahren gemäß Anspruch 2, bei dem die erste Elektrode durch die erste leitfähige Schicht mit dem Chiplet verbunden ist.

5. Verfahren gemäß Anspruch 1, bei dem die erste Elektrode in der ersten leitfähigen Schicht ausgebildet ist.

6. Verfahren gemäß Anspruch 1, bei dem das OLED-Display (10) ferner eine oder mehrere Datensignalleitung(en) (135, 136) und eine oder mehrere Auswahlleitung(en) (137a, 137b) umfasst, und wobei die Stromleitung, die eine oder mehreren Datenleitung(en) und die eine oder mehreren Auswahlleitung(en) in der ersten leitfähigen Schicht ausgebildet und mit entsprechenden Verbindungsplättchen auf dem Chiplet verbunden sind.

7. Verfahren gemäß Anspruch 6, bei dem das Chiplet ferner eine elektrische Durchgangsverbindung umfasst und wobei entweder die Auswahlleitung oder eine Datensignalleitung diskontinuierlich und mit der elektrischen Durchgangsverbindung in dem Chiplet verbunden ist.

8. Verfahren gemäß Anspruch 1, bei dem das OLED-Display ferner eine Signalleitung umfasst, die diskontinuierlich und mit den ersten und letzten Verbindungsplättchen in jeder Reihe von Verbindungsplättchen des Chiplets verbunden ist.

9. Verfahren gemäß Anspruch 1, bei dem die vier durch das Chiplet gesteuerten Pixel jeweils unterschiedliche Farben haben.

10. Verfahren gemäß Anspruch 1, bei dem der Transistorantriebsschaltkreis eines jeden Chiplets einen ersten Transistor mit einem ersten Kanalverhältnis zum Steuern eines ersten Pixels und einen zweiten Antriebstransistor mit einem zweiten Kanalverhältnis zum Steuern eines zweiten Pixels umfasst, wobei der erste Pixel eine andere Farbe hat als der zweite Pixel und das erste Kanalverhältnis anders ist als das zweite Kanalverhältnis.

11. Verfahren nach Anspruch 1, bei dem die Stromleitung (131) über dem Mittelpunkt des Chiplets (120) angeordnet ist.

Revendications

1. Procédé de fabrication d'un affichage à OLED ayant une pluralité de pixels (20a, 20b, 20c, 20d) excités par un courant agencés en rangées et colonnes disposés sur un substrat (100) d'affichage, de telle sorte que lorsqu'un courant est délivré à un pixel, il produit une lumière, l'affichage à OLED comprenant :

(a) chaque pixel ayant des première et deuxième électrodes (161a, 169) et un support (165) électroluminescent réagissant au courant disposé entre les première et deuxième électrodes ;
(b) au moins une micropuce (120, 300) ayant une épaisseur inférieure à 20 micromètres ; incluant un ensemble de circuits (340a, 340b, 340c, 340d) d'excitation à transistors configuré pour commander le fonctionnement d'exactement quatre pixels, la micropuce étant montée sur le substrat (100) d'affichage et ayant des plots de connexion (353a, 353b, 353c, 353d) ; dans lequel la micropuce (120) a une largeur (W) et une longueur (L) qui est plus grande que la largeur (W), et les plots de connexion de la micropuce (120) sont agencés en une première et une deuxième rangée dans le sens de la longueur (L) ;
(c) une couche de planarisation (112) disposée sur au moins une partie de la micropuce ;
(d) une première couche conductrice (133a) disposée sur la couche de planarisation et connectée à au moins un des plots de connexion de la micropuce ; et
(e) un moyen pour délivrer des signaux électriques par l'intermédiaire de la première couche conductrice et d'au moins un des plots de connexion de la micropuce de telle sorte que l'ensemble de circuits d'excitation à transistors de la micropuce commande le courant vers les quatre pixels ;
(f) une ligne d'alimentation (131) agencée parallèle à la largeur (W) de la micropuce ;

le procédé comprenant les étapes suivantes :

- en utilisant une technique au silicium sur isolateur SOI, formation des micropuces (120) comme des circuits intégrés à partir d'un substrat (601) pour circuits intégrés ;
- exécution d'une gravure de dégagement pour séparer partiellement les micropuces du substrat pour circuits intégrés ;
- dotation du substrat (100) d'affichage d'une couche d'adhérence (111) ;
- capture des micropuces avec un poinçon (800) ;
- estampage des micropuces dans la couche d'adhérence ;

et, pour chaque micropuce :

- formation de la couche de planarisation (112) ;
- structuration de la couche de planarisation (112) pour ouvrir des premiers trous de raccordement (143a) ;
- formation de la première couche conductrice

(133a) dans les premiers trous de raccordement (143a) ;
- formation de la première électrode (161a) et connexion de la première électrode (161a) à la première couche conductrice (133a) par l'intermédiaire de deuxièmes trous de raccordement (153a) ;
- formation du support (165) électroluminescent réagissant au courant ; et
- formation de la deuxième électrode (169).

2. Procédé selon la revendication 1, dans lequel la première électrode est formée dans une deuxième couche conductrice qui est différente de la première couche conductrice.

3. Procédé selon la revendication 2 incluant en outre une couche d'isolateur disposée entre au moins une partie de la première électrode et la première couche conductrice.

4. Procédé selon la revendication 2, dans lequel la première électrode est connectée à la micropuce par la première couche conductrice.

5. Procédé selon la revendication 1, dans lequel la première électrode est formée dans la première couche conductrice.

6. Procédé selon la revendication 1, dans lequel l'affichage à OLED inclut en outre une ou plusieurs ligne(s) (135, 136) de signaux de données et une ou plusieurs ligne(s) (137a, 137b) de sélection et dans lequel ladite ligne d'alimentation, ladite une ou lesdites plusieurs ligne(s) de signaux de données et ladite une ou lesdites plusieurs ligne(s) de sélection sont formées dans la première couche conductrice et connectées à des plots de connexion correspondants sur la micropuce.

7. Procédé selon la revendication 6, dans lequel la micropuce comprend en outre une interconnexion électrique et dans lequel soit la ligne de sélection, soit la ligne de signaux de données est discontinue et connectée à l'interconnexion électrique dans la micropuce.

8. Procédé selon la revendication 1, dans lequel l'affichage à OLED inclut en outre une ligne de signaux qui est discontinue et connectée au premier et au dernier plot de connexion dans chaque rangée de plots de connexion de la micropuce.

9. Procédé selon la revendication 1, dans lequel les quatre pixels commandés par la micropuce ont chacun des couleurs différentes.

10. Procédé selon la revendication 1, dans lequel l'ensemble de circuits d'excitation à transistors de chaque micropuce inclut un premier transistor d'excitation ayant un premier rapport de canal pour commander un premier pixel et un deuxième transistor d'excitation ayant un deuxième rapport de canal pour commander un deuxième pixel où le premier pixel a une couleur différente du deuxième pixel et le premier rapport de canal est différent du deuxième rapport de canal.

11. Procédé selon la revendication 1, dans lequel la ligne d'alimentation (131) est disposée au centre de la micropuce (120).

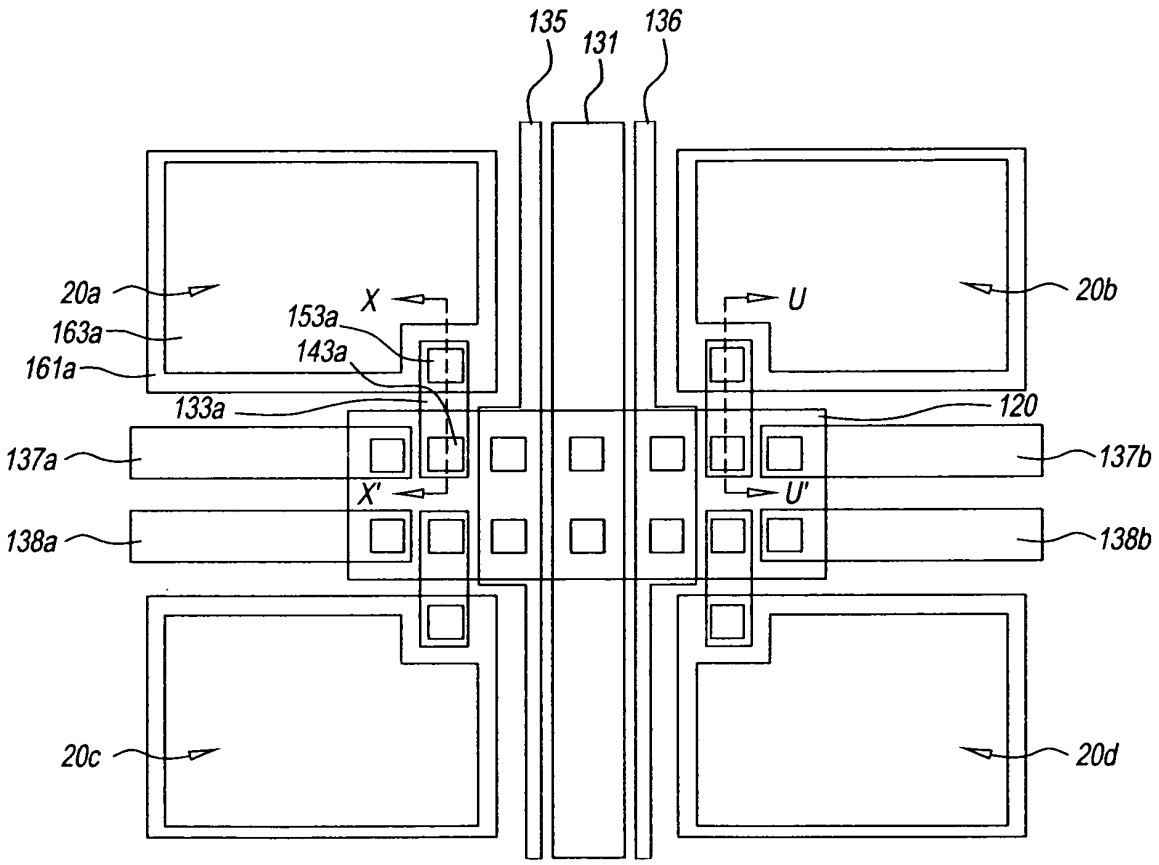
135
131
136
20a
163a
161a
153a
143a
X
X'
U
U'
20b
133a
120
137a
137b
138a
138b
20c
20d

FIG. 1

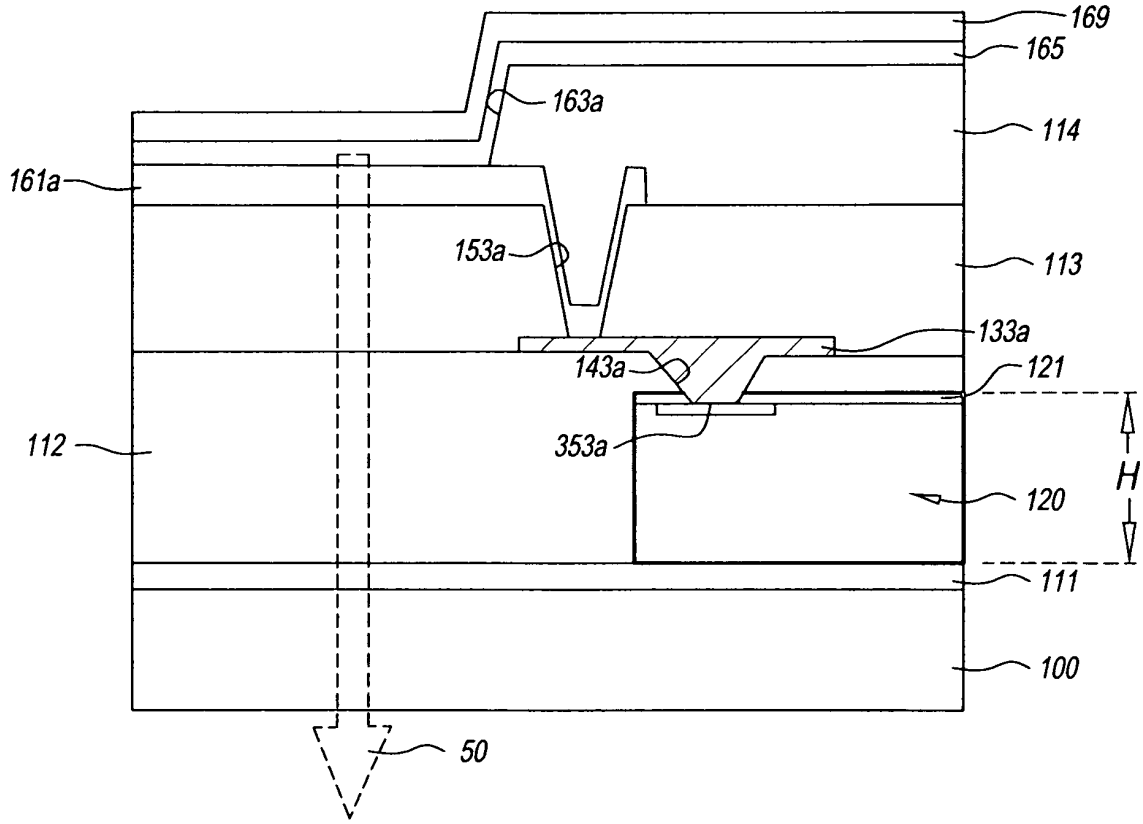
169
165
163a
114
161a
153a
113
133a
143a
121
112
353a
H
120
111
100
50

FIG. 2A

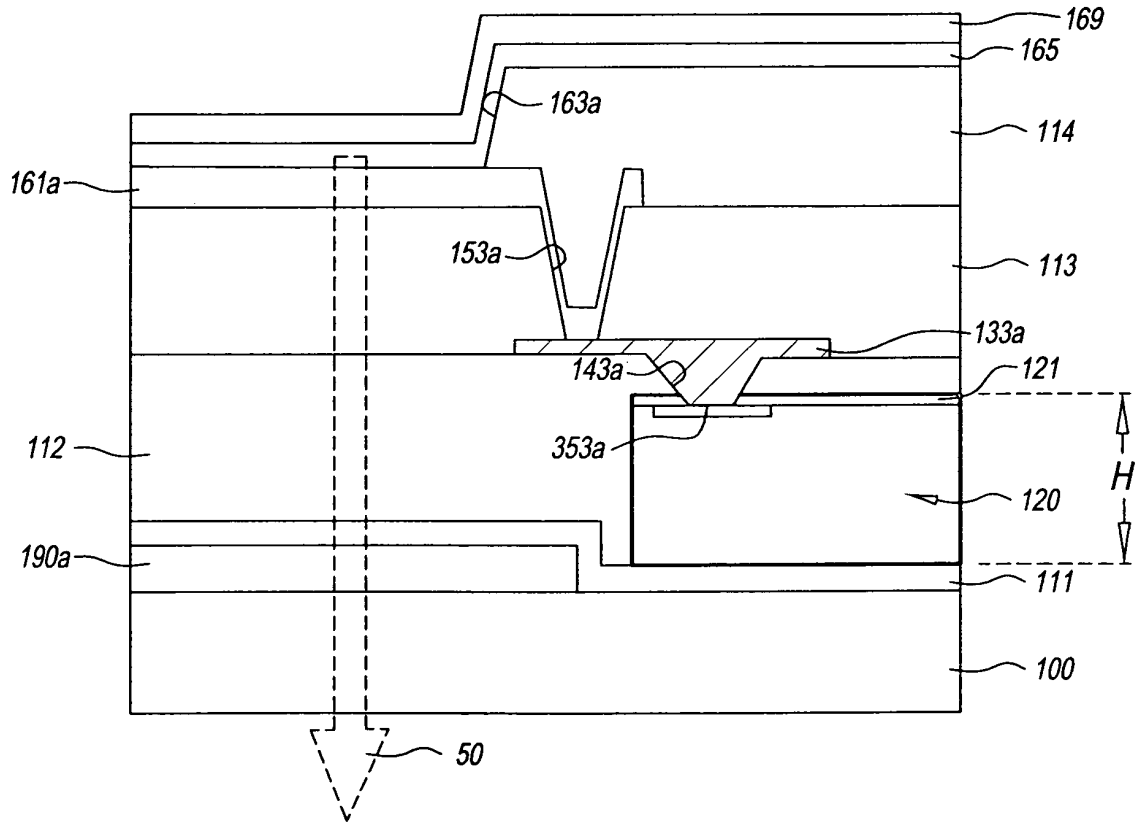
169
165
163a
114
161a
153a
113
133a
143a
121
112
353a
H
120
190a
111
100
50

FIG. 2B

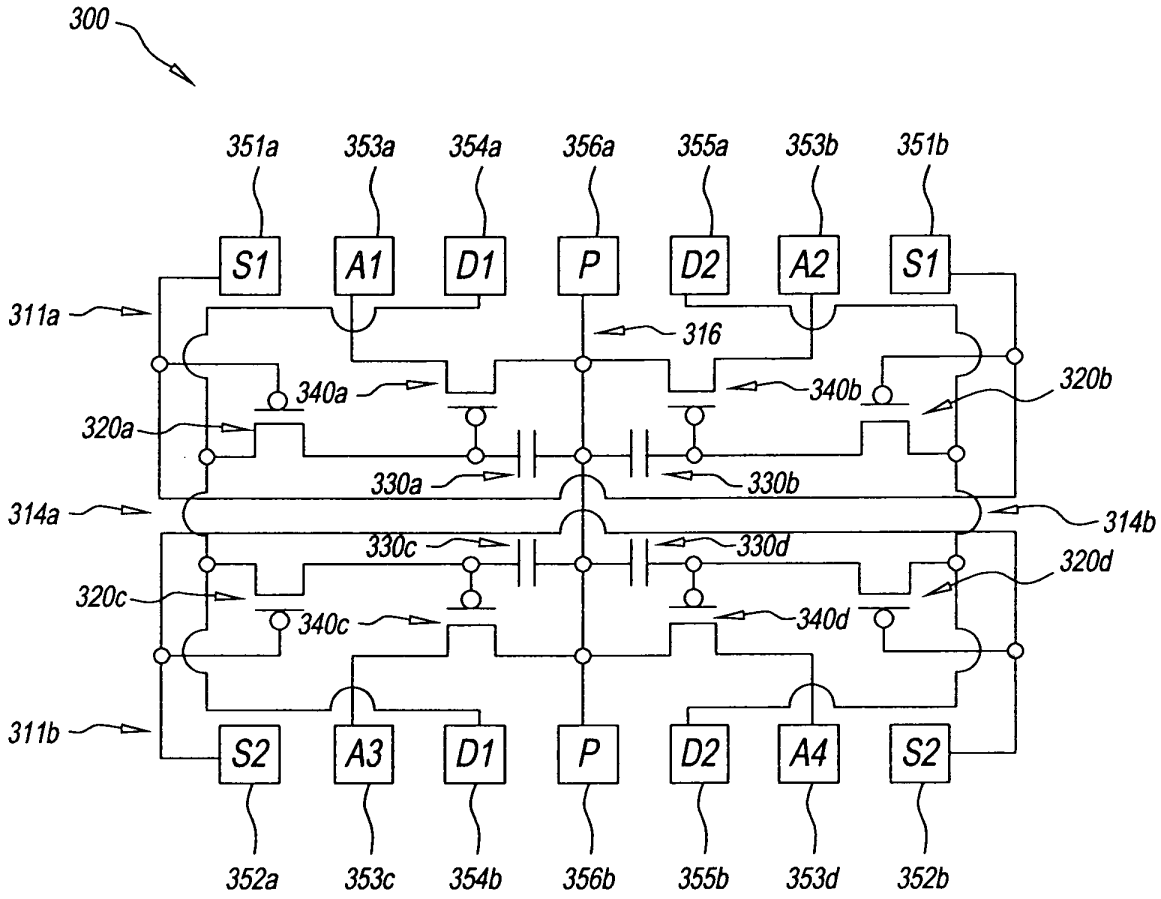
300
351a
353a
354a
356a
355a
353b
351b
S1
A1
D1
P
D2
A2
S1
311a
316
340a
340b
320b
320a
330a
330b
314a
314b
330c
330d
320d
320c
340c
340d
311b
S2
A3
D1
P
D2
A4
S2
352a
353c
354b
356b
355b
353d
352b

FIG. 3A

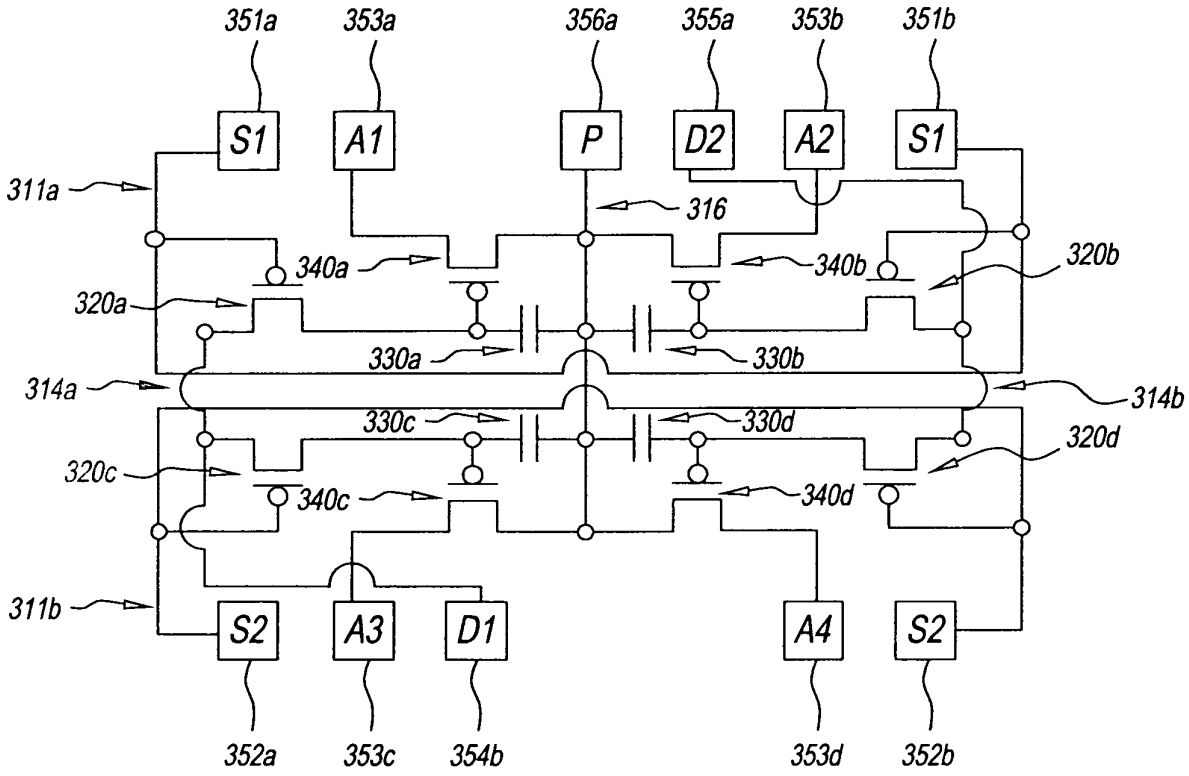
351a
353a
356a
355a
353b
351b
S1
A1
P
D2
A2
S1
311a
316
340a
340b
320b
320a
330a
330b
314a
314b
330c
330d
320d
320c
340c
340d
311b
S2
A3
D1
A4
S2
352a
353c
354b
353d
352b

FIG. 3B

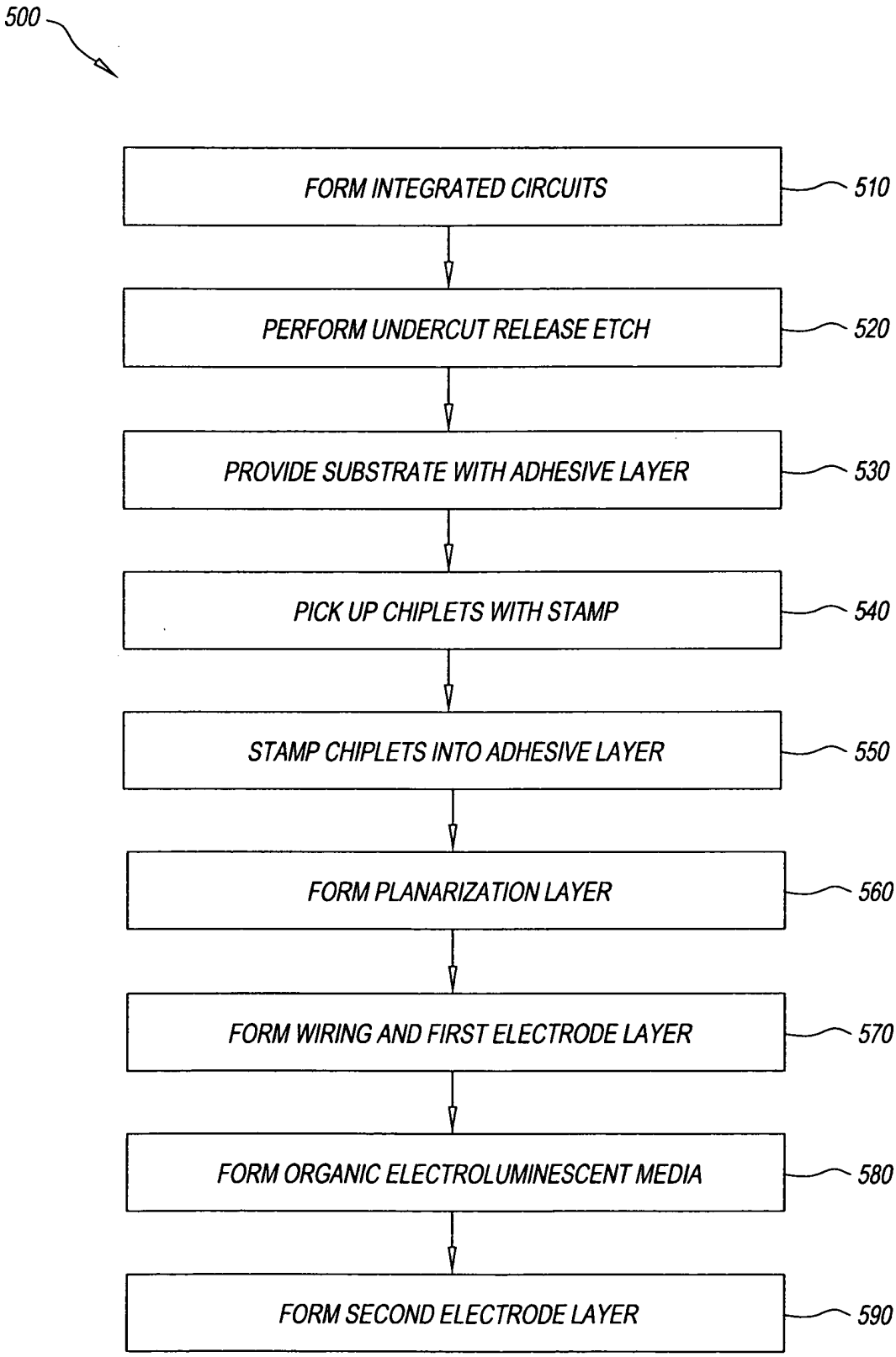
500
FORM INTEGRATED CIRCUITS
510
PERFORM UNDERCUT RELEASE ETCH
520
PROVIDE SUBSTRATE WITH ADHESIVE LAYER
530
PICK UP CHIPLETS WITH STAMP
540
STAMP CHIPLETS INTO ADHESIVE LAYER
550
FORM PLANARIZATION LAYER
560
FORM WIRING AND FIRST ELECTRODE LAYER
570
FORM ORGANIC ELECTROLUMINESCENT MEDIA
580
FORM SECOND ELECTRODE LAYER
590

FIG. 4

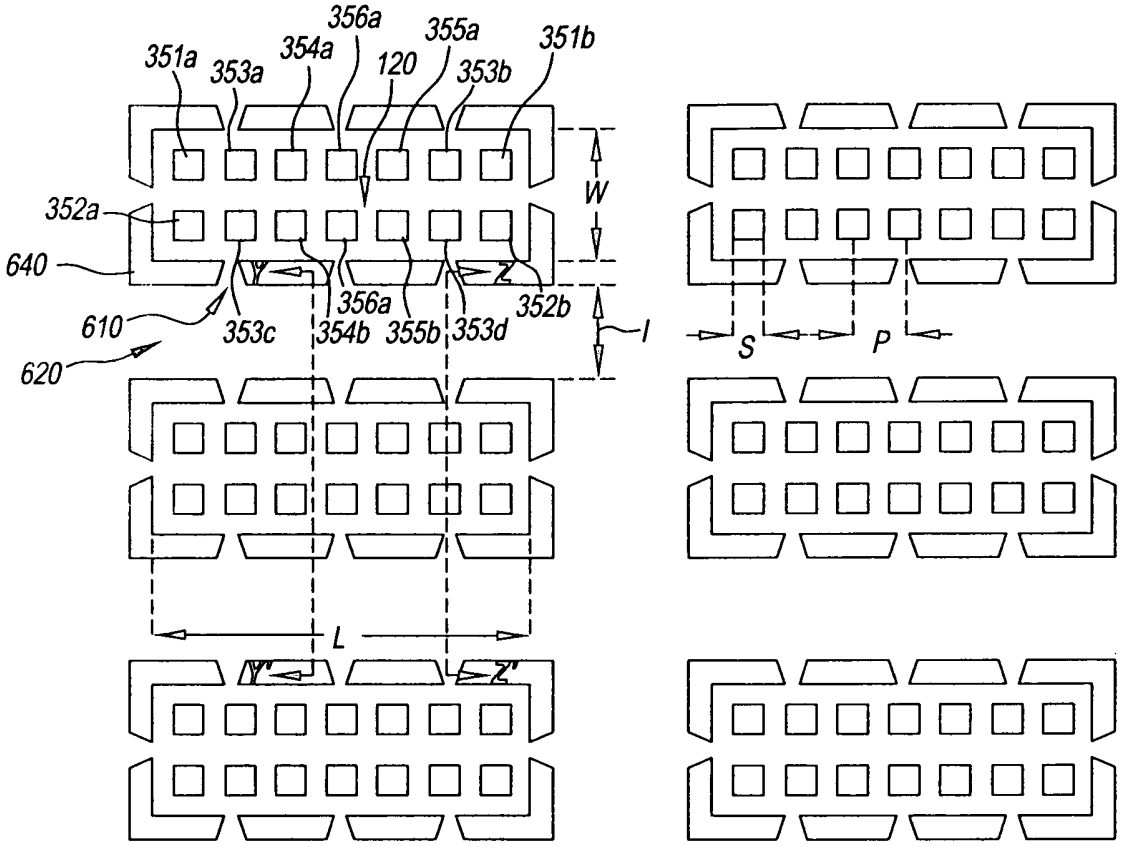
356a
355a
351a
353a
354a
120
353b
351b
W
352a
640
Y
Z
610
620
353c
354b
356a
355b
353d
352b
l
S
P
L
Y'
Z'

FIG. 5

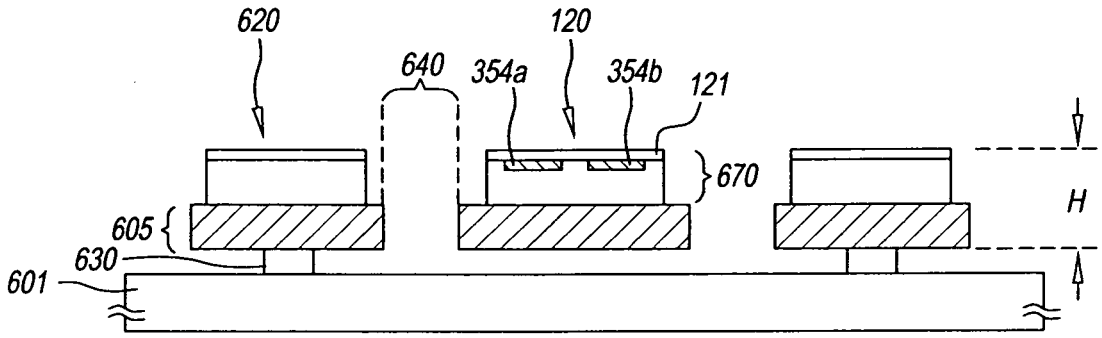
620
640
120
354a
354b
121
670
H
605
630
601

FIG. 6A

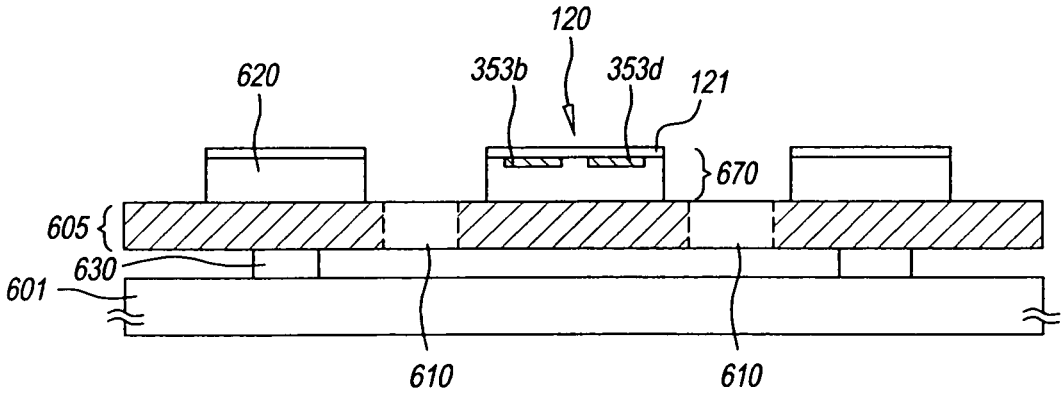
120
620
353b
353d
121
670
605
630
601
610
610

FIG. 6B

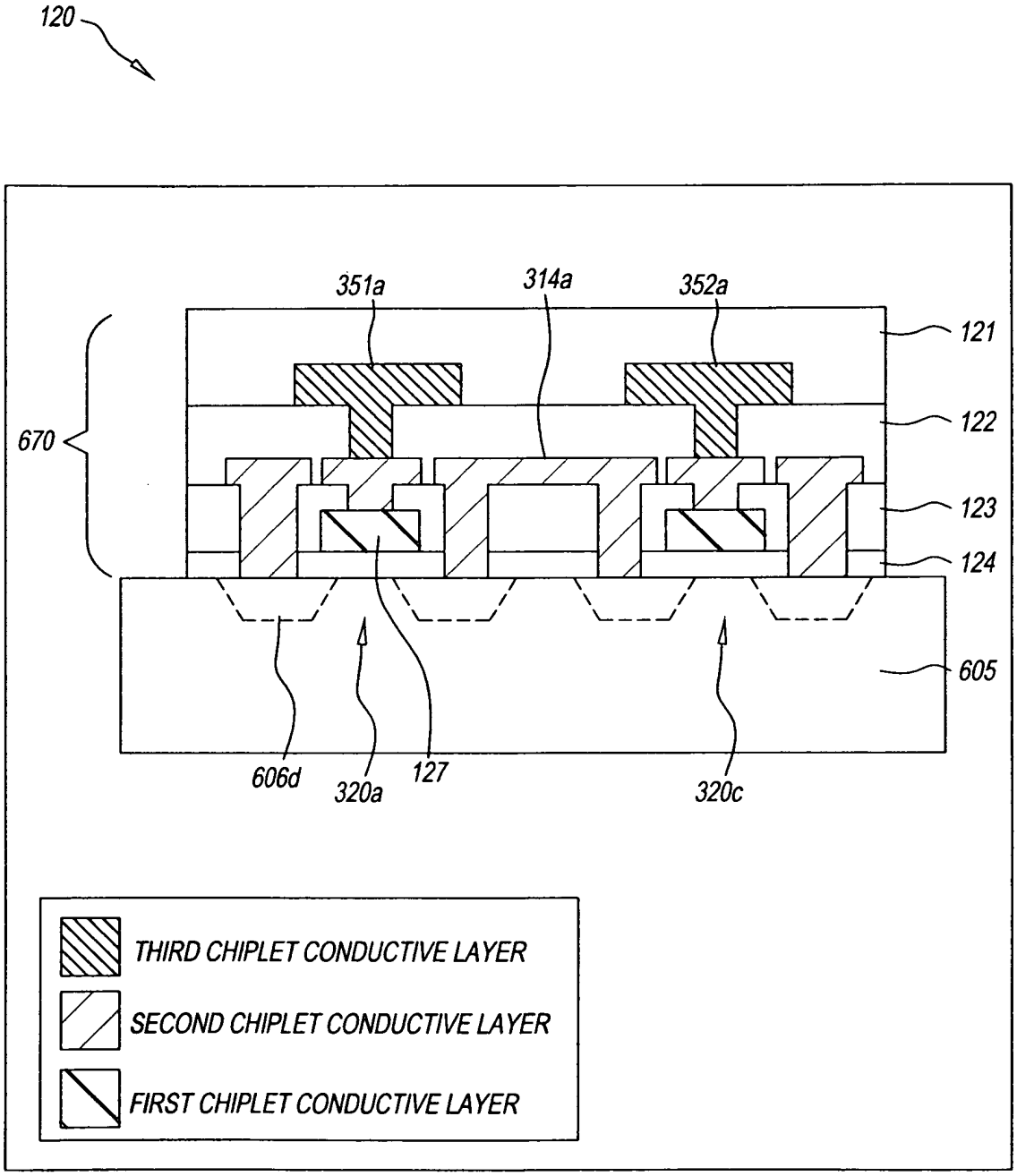
120
351a
314a
352a
121
122
123
124
670
605
606d
320a
127
320c
THIRD CHIPLET CONDUCTIVE LAYER
SECOND CHIPLET CONDUCTIVE LAYER
FIRST CHIPLET CONDUCTIVE LAYER

FIG. 7

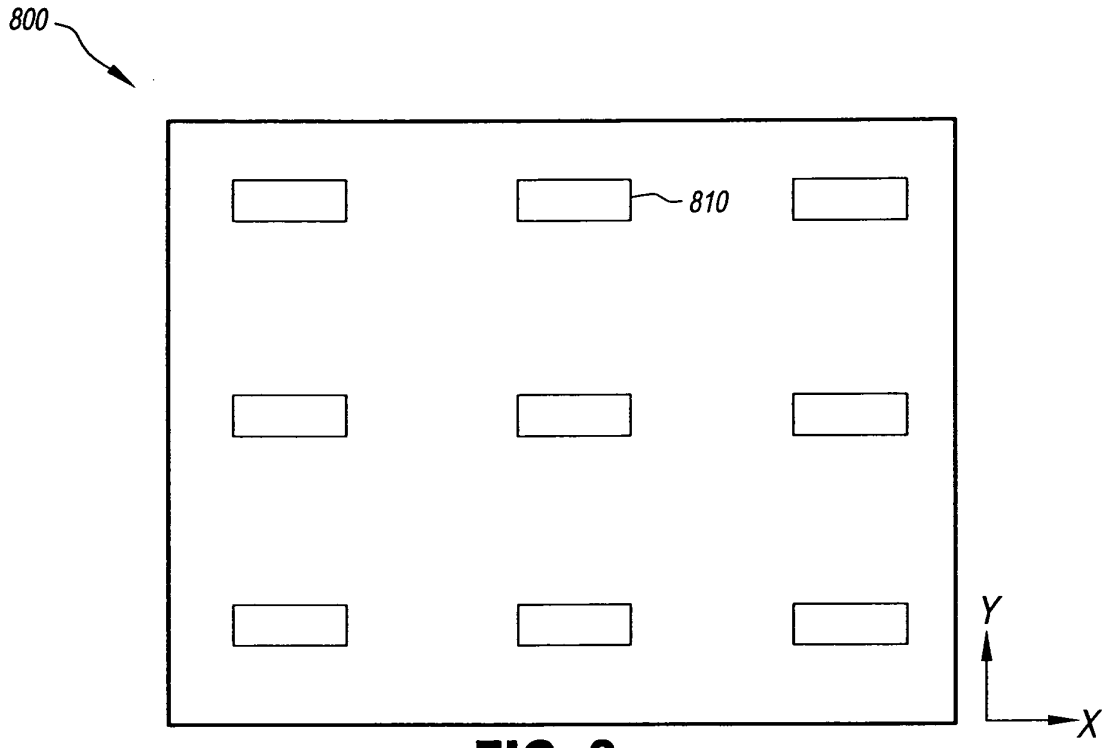

FIG. 8

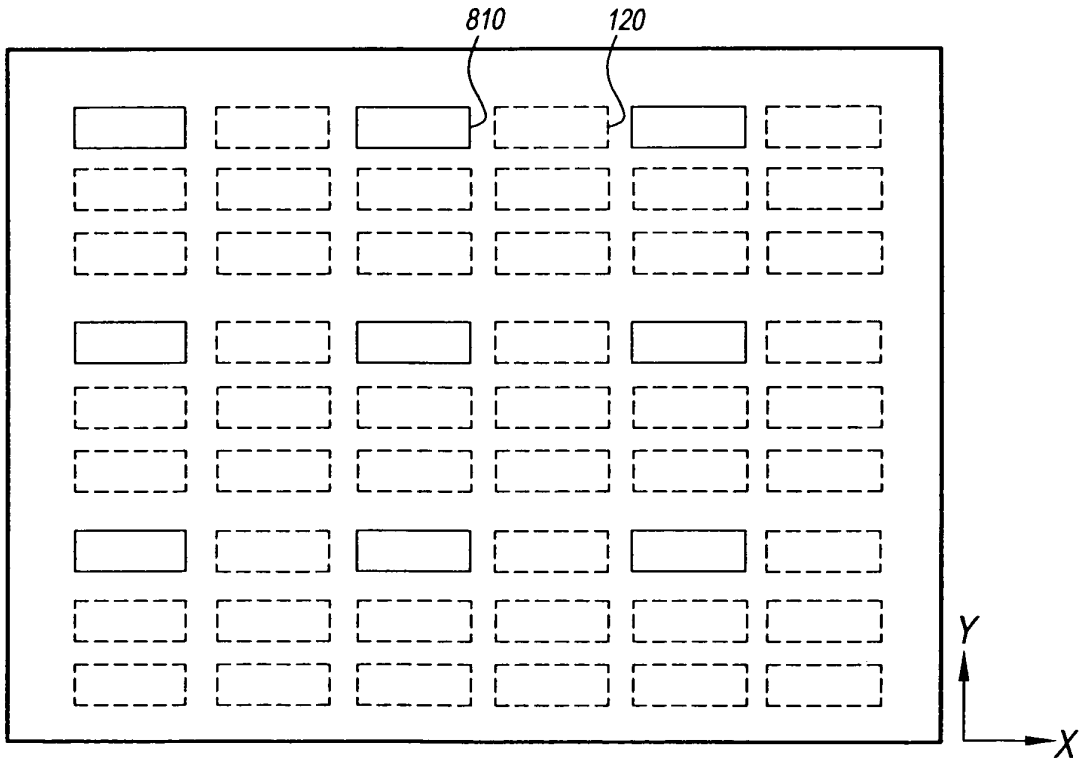

FIG. 9

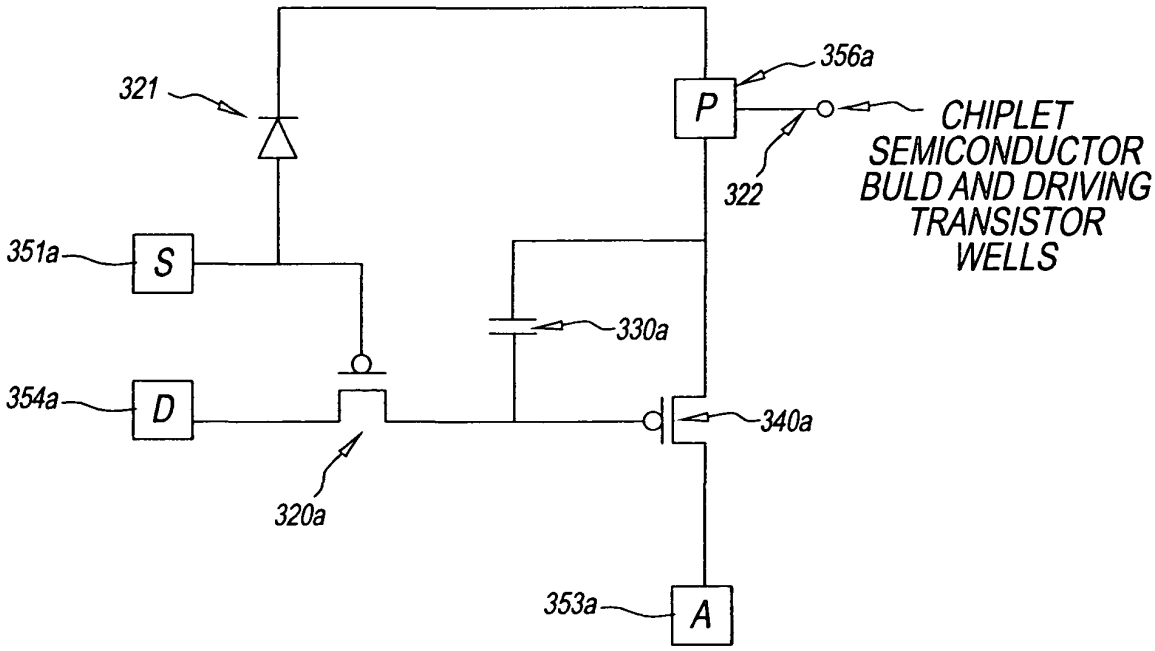
321
356a
P
CHIPLET SEMICONDUCTOR BULD AND DRIVING TRANSISTOR WELLS
322
351a
S
330a
354a
D
340a
320a
353a
A

FIG. 10

REFERENCES CITED IN THE DESCRIPTION

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专利名称(译)	具有嵌入式芯片驱动的OLED显示装置及其制造方法		
公开(公告)号	EP2324507B1	公开(公告)日	2016-01-06
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[标]申请(专利权)人(译)	全球OLED TECH 桑普司公司		
申请(专利权)人(译)	全球OLED科技有限责任公司 Semprius公司INC.		
当前申请(专利权)人(译)	Semprius公司INC. 全球OLED科技有限责任公司		
[标]发明人	WINTERS DUSTIN LEE HAMER JOHN WILLIAM PARRETT GARY BOWER CHRISTOPHER MENARD ETIENNE		
发明人	WINTERS, DUSTIN, LEE HAMER, JOHN, WILLIAM PARRETT, GARY BOWER, CHRISTOPHER MENARD, ETIENNE		
IPC分类号	H01L27/32		
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优先权	12/191478 2008-08-14 US		
其他公开文献	EP2324507A1		
外部链接	Espacenet		

摘要(译)

一种电致发光器件，具有以行和列排列的多个电流驱动像素，使得当向像素提供电流时，它产生光，包括具有第一和第二电极的每个像素以及设置在第一和第二电极之间的电流响应电致发光介质;至少一个小芯片，厚度小于20微米;包括晶体管驱动电路，用于控制至少四个像素的操作，小芯片安装在基板上并具有连接焊盘;平面化层设置在小芯片的至少一部分上;平坦化层上方的第一导电层并连接至至少一个连接焊盘;以及用于通过第一导电层和小芯片的至少一个连接焊盘提供电信号的结构，使得小芯片的晶体管驱动电路控制到四个像素的电流。

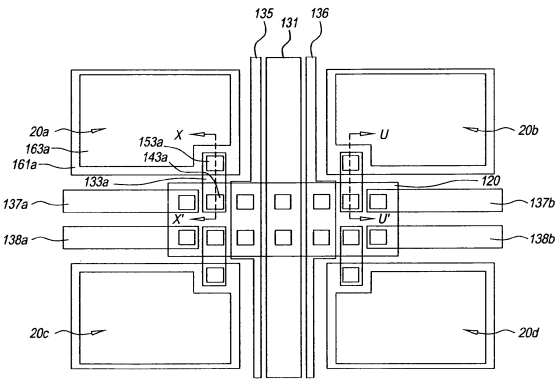

FIG. 1